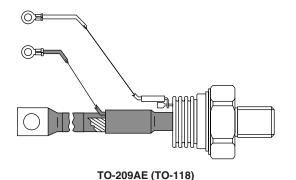


### Vishay High Power Products

# Phase Control Thyristors (Stud Version), 330 A



| PRODUCT SUMMARY    |       |  |
|--------------------|-------|--|
| I <sub>T(AV)</sub> | 330 A |  |

### **FEATURES**

- Center amplifying gate
- International standard case TO-209AE (TO-118)





- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Lead (Pb)-free
- Designed and qualified for industrial level

#### **TYPICAL APPLICATIONS**

- · DC motor controls
- Controlled DC power supplies
- AC controllers

| MAJOR RATINGS AND CHARACTERISTICS  |                 |             |                   |  |
|------------------------------------|-----------------|-------------|-------------------|--|
| PARAMETER                          | TEST CONDITIONS | VALUES      | UNITS             |  |
| 1                                  |                 | 330         | A                 |  |
| $I_{T(AV)}$                        | T <sub>C</sub>  | 75          | °C                |  |
| I <sub>T(RMS)</sub>                |                 | 520         |                   |  |
|                                    | 50 Hz           | 9000        | Α                 |  |
| I <sub>TSM</sub>                   | 60 Hz           | 9420        |                   |  |
| 12).                               | 50 Hz           | 405         | kA <sup>2</sup> s |  |
| I <sup>2</sup> t                   | 60 Hz           | 370         | KA-S              |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> |                 | 400 to 2000 | V                 |  |
| t <sub>q</sub>                     | Typical         | 100         | μs                |  |
| T <sub>J</sub>                     |                 | - 40 to 125 | °C                |  |

### **ELECTRICAL SPECIFICATIONS**

| VOLTAGE R   | VOLTAGE RATINGS |  |  |   |  |  |  |  |
|-------------|-----------------|--|--|---|--|--|--|--|
| TYPE NUMBER | VOLTAGE<br>CODE | V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK<br>AND OFF-STATE VOLTAGE<br>V | V <sub>RSM</sub> , MAXIMUM<br>NON-REPETITIVE PEAK VOLTAGE<br>V | $I_{DRM}/I_{RRM}$ MAXIMUM<br>AT $T_J = T_J$ MAXIMUM<br>mA |  |  |  |  |
|             | 04              | 400  | 500  |   |  |  |  |  |
|             | 08              | 800  | 900  |   |  |  |  |  |
| ST330S      | 12              | 1200   | 1300   | 50  |  |  |  |  |
|             | 16              | 1600   | 1700   |   |  |  |  |  |
|             | 20              | 2000   | 2100   |   |  |  |  |  |

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## ST330SPbF Series

# Vishay High Power Products Phase Control Thyristors (Stud Version), 330 A



| ABSOLUTE MAXIMUM RATIN                        | GS                  |  |                                  |   |        |                     |
|---|---------------------|--|----------------------------------|---|--------|---------------------|
| PARAMETER                                     | SYMBOL              | TEST CONDITIONS  |                                  |   | VALUES | UNITS               |
| Maximum average on-state current              | -                   | 180° condu   | 180° conduction, half sine wave  |   | 330    | Α                   |
| at case temperature                           | $I_{T(AV)}$         |  |                                  |   | 75     | °C                  |
| Maximum RMS on-state current                  | I <sub>T(RMS)</sub> | DC at 75 °C  | case temperati                   | ure   | 520    |                     |
|   |                     | t = 10 ms  | No voltage                       |   | 9000   | A kA <sup>2</sup> s |
| Maximum peak, one-cycle                       | I                   | t = 8.3 ms   | reapplied                        |   | 9420   |                     |
| non-repetitive surge current                  | I <sub>TSM</sub>    | t = 10 ms  | 100 % V <sub>RRM</sub>           |   | 7570   |                     |
|   |                     | t = 8.3 ms   | reapplied                        | Sinusoidal half wave,                           | 7920   |                     |
| Mariana 124 for fraince                       | l <sup>2</sup> t    | t = 10 ms  | No voltage                       | initial T <sub>J</sub> = T <sub>J</sub> maximum | 405    |                     |
|   |                     | t = 8.3 ms   | reapplied                        |   | 370    |                     |
| Maximum I <sup>2</sup> t for fusing           |                     | t = 10 ms  | 100 % V <sub>RRM</sub>           |   | 287    |                     |
|   |                     | t = 8.3 ms   | reapplied                        |   | 262    |                     |
| Maximum $I^2\sqrt{t}$ for fusing              | I <sup>2</sup> √t   | t = 0.1 to 10 ms, no voltage reapplied   |                                  | 4050  | kA²√s  |                     |
| Low level value of threshold voltage          | V <sub>T(TO)1</sub> | (16.7 % x π  | $x I_{T(AV)} < I < \pi x$        | $I_{T(AV)}$ ), $T_J = T_J$ maximum              | 0.834  | V                   |
| High level value of threshold voltage         | V <sub>T(TO)2</sub> | $(I > \pi \times I_{T(AV)})$   | $()$ , $T_J = T_J \text{ maxim}$ | mum   | 0.898  | V                   |
| Low level value of on-state slope resistance  | r <sub>t1</sub>     | (16.7 % x $\pi$ x $I_{T(AV)}$ < $I$ < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum     |                                  | 0.687   | mΩ     |                     |
| High level value of on-state slope resistance | r <sub>t2</sub>     | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$                              |                                  | 0.636   | 1115.2 |                     |
| Maximum on-state voltage                      | $V_{TM}$            | $I_{pk} = 1000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$ |                                  | 1.52  | V      |                     |
| Maximum holding current                       | lΗ                  | T 25 °C  | anode cupply 1                   | 2 V resistive load                              | 600    | mA                  |
| Typical latching current                      | ΙL                  | T <sub>J</sub> = 25 °C, anode supply 12 V resistive load                             |                                  | 1000  | ] ""^  |                     |

| SWITCHING  |                |   |        |       |
|--|----------------|---|--------|-------|
| PARAMETER  | SYMBOL         | TEST CONDITIONS   | VALUES | UNITS |
| Maximum non-repetitive rate of rise of turned-on current | dl/dt          | Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$<br>$T_J = T_J$ maximum, anode voltage $\le 80~\%$ $V_{DRM}$  | 1000   | A/µs  |
| Typical delay time                                       | t <sub>d</sub> | Gate current A, $dl_g/dt = 1$ A/ $\mu$ s $V_d = 0.67 \% V_{DRM}$ , $T_J = 25 °C$  | 1.0    |       |
| Typical turn-off time                                    | t <sub>q</sub> | $I_{TM} = 550 \text{ A, } T_J = T_J \text{ maximum, } dI/dt = 40 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, } dV/dt = 20 \text{ V/}\mu\text{s, } \text{ gate } 0 \text{ V } 100 \Omega\text{, } t_p = 500 \mu\text{s}$ | 100    | μs    |

| BLOCKING   |                                       |  |        |       |
|--|---------------------------------------|--|--------|-------|
| PARAMETER  | SYMBOL                                | TEST CONDITIONS                                      | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt                                 | $T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$   | 500    | V/µs  |
| Maximum peak reverse and off-state leakage current | I <sub>RRM,</sub><br>I <sub>DRM</sub> | $T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied | 50     | mA    |

Document Number: 94409 Revision: 11-Aug-08



# Phase Control Thyristors (Stud Version), 330 A

## Vishay High Power Products

| TRIGGERING                          |                    |                                     |  |        |      |       |  |
|-------------------------------------|--------------------|-------------------------------------|--|--------|------|-------|--|
| PARAMETER                           | SYMBOL             | TEGT COMPITIONS                     |  | VALUES |      | шито  |  |
| PARAMETER                           | STIVIBUL           | l Ex                                | ST CONDITIONS  | TYP.   | MAX. | UNITS |  |
| Maximum peak gate power             | P <sub>GM</sub>    | $T_J = T_J$ maximum,                | t <sub>p</sub> ≤ 5 ms  | 10.0   |      | W     |  |
| Maximum average gate power          | P <sub>G(AV)</sub> | $T_J = T_J$ maximum,                | f = 50 Hz, d% = 50   | 2      | .0   | VV    |  |
| Maximum peak positive gate current  | I <sub>GM</sub>    | $T_J = T_J$ maximum,                | t <sub>p</sub> ≤ 5 ms  | 3      | .0   | Α     |  |
| Maximum peak positive gate voltage  | + V <sub>GM</sub>  | T - T movimum                       |  |        | 20   |       |  |
| Maximum peak negative gate voltage  | - V <sub>GM</sub>  | $T_J = T_J$ maximum, $t_p \le 5$ ms |  | 5.0    |      | V     |  |
|                                     | I <sub>GT</sub>    | T <sub>J</sub> = - 40 °C            | Maximum required gate trigger/   | 200    | -    |       |  |
| DC gate current required to trigger |                    | T <sub>J</sub> = 25 °C              |  | 100    | 200  | mA    |  |
|                                     |                    | T <sub>J</sub> = 125 °C             | current/voltage are the lowest   |        | -    |       |  |
|                                     |                    | T <sub>J</sub> = - 40 °C            | value which will trigger all units   | 2.5    | -    |       |  |
| DC gate voltage required to trigger | $V_{GT}$           | T <sub>J</sub> = 25 °C              | 12 V anode to cathode applied  | 1.8    | 3    | ٧     |  |
|                                     |                    | T <sub>J</sub> = 125 °C             |  | 1.1    | -    |       |  |
| DC gate current not to trigger      | I <sub>GD</sub>    | T - T movimum                       | Maximum gate current/voltage not to trigger is the maximum                                 |        | 0    | mA    |  |
| DC gate voltage not to trigger      | $V_{\mathrm{GD}}$  | $T_J = T_J$ maximum                 | value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied | 0.25   |      | V     |  |

| THERMAL AND MECHANICAL SPECIFICATIONS        |                     |  |               |                     |  |
|--|---------------------|--|---------------|---------------------|--|
| PARAMETER                                    | SYMBOL              | TEST CONDITIONS                              | VALUES        | UNITS               |  |
| Maximum operating junction temperature range | TJ                  |  | - 40 to 125   | °C                  |  |
| Maximum storage temperature range            | T <sub>Stg</sub>    |  | - 40 to 150   |                     |  |
| Maximum thermal resistance, junction to case | R <sub>thJC</sub>   | DC operation                                 | 0.10          | K/W                 |  |
| Maximum thermal resistance, case to heatsink | R <sub>thC-hs</sub> | Mounting surface, smooth, flat and greased   | 0.03          | TN/VV               |  |
| Mounting torque, ± 10 %                      |                     | Non-lubricated threads                       | 48.5<br>(425) | N ⋅ m<br>(lbf ⋅ in) |  |
| Approximate weight                           |                     |  | 535           | g                   |  |
| Case style                                   |                     | See dimension - link at the end of datasheet | TO-209AE (    | TO-118)             |  |

| △R <sub>thJC</sub> CONDUCTION |                       |                        |                     |       |  |
|-------------------------------|-----------------------|------------------------|---------------------|-------|--|
| CONDUCTION ANGLE              | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS     | UNITS |  |
| 180°                          | 0.011                 | 0.008                  |                     |       |  |
| 120°                          | 0.013                 | 0.014                  |                     |       |  |
| 90°                           | 0.017                 | 0.018                  | $T_J = T_J$ maximum | K/W   |  |
| 60°                           | 0.025                 | 0.026                  |                     |       |  |
| 30°                           | 0.041                 | 0.042                  |                     |       |  |

#### Note

 $<sup>\</sup>bullet \ \ \, \text{The table above shows the increment of thermal resistance } \, R_{\text{thJC}} \, \text{when devices operate at different conduction angles than DC} \,$ 

# Vishay High Power Products Phase Control Thyristors (Stud Version), 330 A



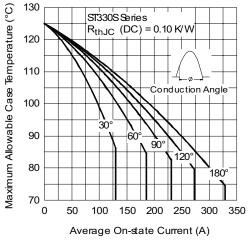


Fig. 1 - Current Ratings Characteristics

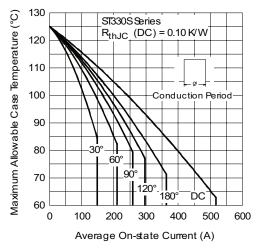


Fig. 2 - Current Ratings Characteristics

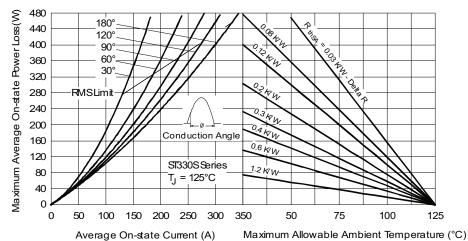


Fig. 3 - On-State Power Loss Characteristics

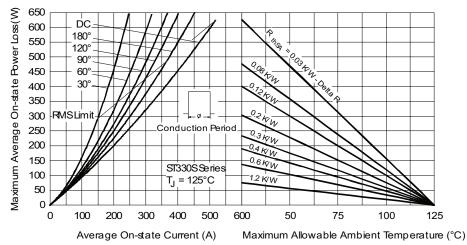
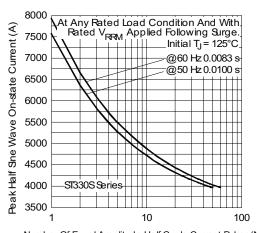


Fig. 4 - On-State Power Loss Characteristics



## Phase Control Thyristors (Stud Version), 330 A

## Vishay High Power Products



Number Of Equal Amplitude Half Cycle Current Pulses (N) Fig. 5 - Maximum Non-Repetitive Surge Current

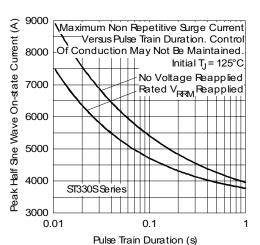


Fig. 6 - Maximum Non-Repetitive Surge Current

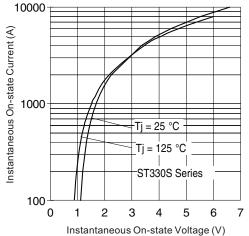


Fig. 7 - On-State Voltage Drop Characteristics

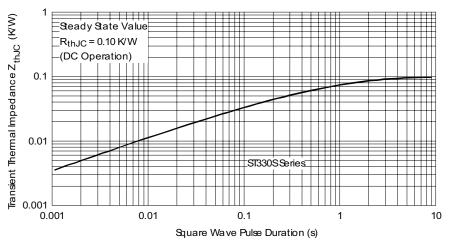
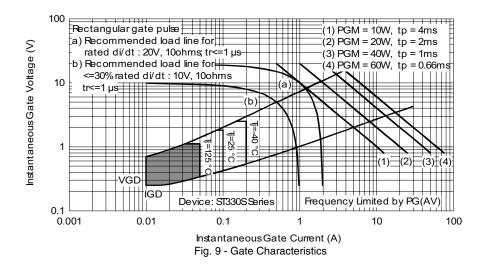


Fig. 8 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

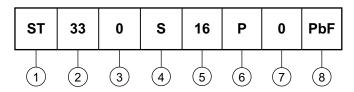
# Vishay High Power Products Phase Control Thyristors (Stud Version), 330 A





#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Thyristor

2 - Essential part number

3 - 0 = Converter grade

4 - S = Compression bonding stud

Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

P = Stud base 3/4"-16UNF-2A threads

7 - 0 = Eyelet terminals (gate and auxiliary cathode leads)

1 = Fast-on terminals (gate and auxiliary cathode leads)

8 - Lead (Pb)-free

| LINKS TO RELAT | TED DOCUMENTS                   |
|----------------|---------------------------------|
| Dimensions     | http://www.vishay.com/doc?95080 |

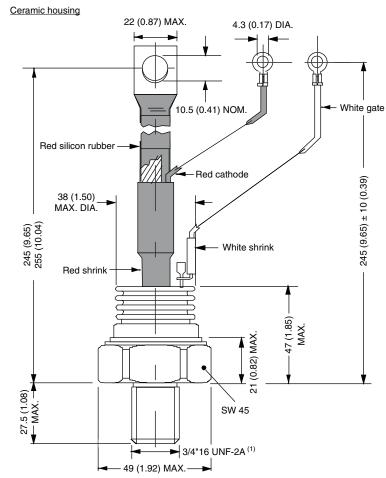
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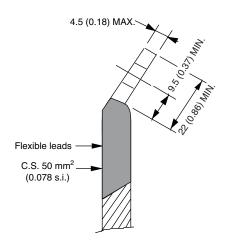


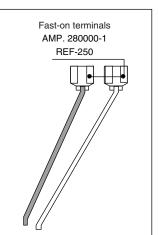
Vishay Semiconductors

## **TO-209AE (TO-118)**

### **DIMENSIONS** in millimeters (inches)







#### Note

(1) For metric device: M24 x 1.5 - length 21 (0.83) maximum



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TD250N16KOF-A VS-ST110S16P0 VS-10RIA10 VS-16TTS08-M3 TS110-7A1-AP T930N36TOF VT T2160N24TOF VT